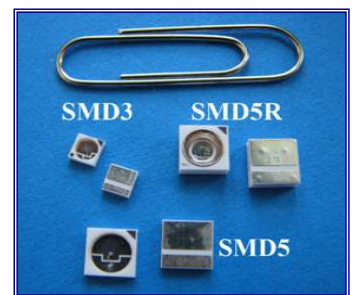
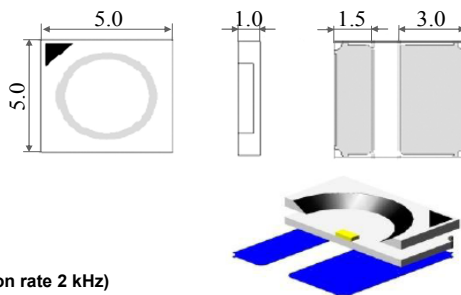
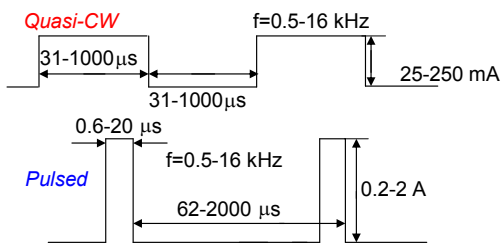
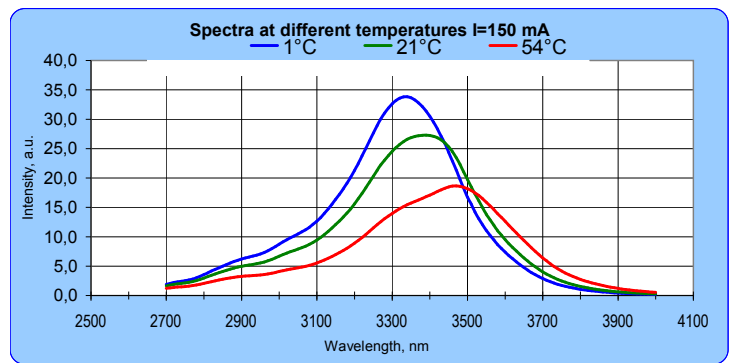
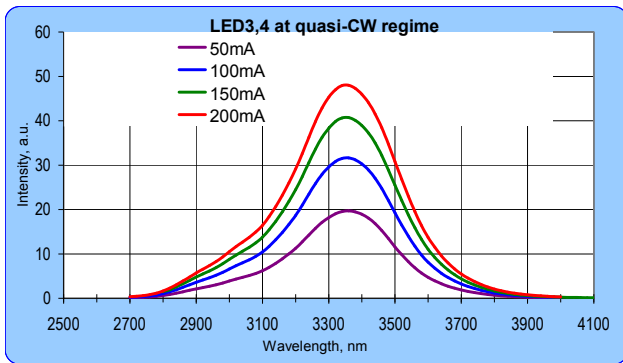


Light Emitting Diodes with central wavelength 3,40 μm series are based on heterostructures grown on InAs substrates by MOCVD. InAs is used in the active layer. Wide band gap solid solutions InAsSbP with P content 50% are used for good electron confinement.

| Parameters | Units | Conditions | Ratings | | |
|---|---------------------------------------|------------|------------------------|------|------|
| | | | Min | Typ | Max |
| Peak emission wavelength | μm | T=300 K | 3,32 | 3,40 | 3,46 |
| FWHM of the emission band | nm | 150 mA CW | 400 | 500 | 600 |
| Quasi-CW Optical Power | μW | 200 mA qCW | 25 | 35 | 45 |
| Pulsed Optical Power | μW | 1 A | 320 | 400 | 480 |
| Switching Time | ns | T=300 K | 10 | 20 | 30 |
| Operating Temperature Range, $^{\circ}\text{C}$ | -240 $^{\circ}$ \div +50 $^{\circ}$ | | | | |
| Emitting Area, μm | 300x300 | | | | |
| Soldering temperature | 260 $^{\circ}\text{C}$ | | | | |
| Package | | | | | |
| SMD type package 3x3 mm based on high thermal conductivity ceramics | | | MID IR LED-SMD3 | | |
| SMD type package 5x5 mm based on high thermal conductivity ceramics | | | MID IR LED-SMD5 | | |
| SMD type package 5x5 mm based on high thermal conductivity ceramics with microreflector | | | MID IR LED-SMD5R | | |



Maximum current is 220 mA at quasi-CW
Maximum pulsed current is 1 A (duration 500 ns, repetition rate 2 kHz)
Optimal operating current is 150-200 mA at quasi-CW.

